

ABSTRACT OF THE DISCLOSURE

An AlN layer having a surface of a texture structure is formed on a sapphire substrate. Then, a growth suppressing material layer is formed on the AlN layer so that the AlN layer is partially exposed to the outside. Then, group III nitride compound semiconductor layers are grown on the AlN layer and on the growth suppressing material layer by execution of an epitaxial lateral overgrowth method. Thus, a group III nitride compound semiconductor device is produced. An undercoat layer having convex portions each shaped like a truncated hexagonal pyramid is formed on a substrate. Group III nitride compound semiconductor layers having a device function are laminated successively on the undercoat layer.

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